

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	I_D max $T_A = +25^\circ C$
60V	80m Ω @ $V_{GS} = 10V$	4.1A
	100m Ω @ $V_{GS} = 4.5V$	3.6A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

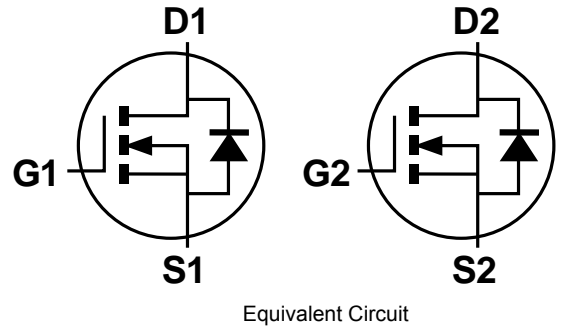
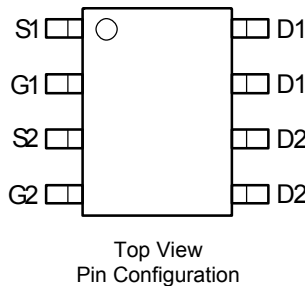
Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe Solderable per MIL-STD-202, Method 208
- Weight: 0.074 grams (Approximate)

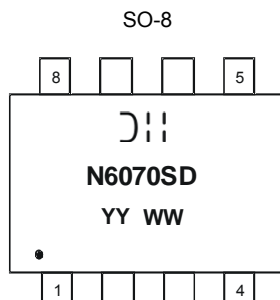


Ordering Information (Note 4)

Part Number	Case	Packaging
DMN6070SSD-13	SO-8	2,500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



☺|| = Manufacturer's Marking
 N6070SD = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Year (ex: 13 = 2013)
 WW = Week (01 - 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	60	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State I _D	T _A = +25°C	3.3
		T _A = +70°C	2.6
	t < 10s I _D	T _A = +25°C	4.1
		T _A = +70°C	3.4
Maximum Continuous Body Diode Forward Current (Note 5)	I _S	2.0	A
Pulsed Drain Current (10μs pulse, duty cycle = 1%)	I _{DM}	12	A
Avalanche Current (Note 7) L=0.1mH	I _{AS}	10	A
Avalanche Energy (Note 7) L=0.1mH	E _{AS}	5.9	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P _D	1.2	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State R _{θJA}	104	°C/W
		t < 10s 61	
Total Power Dissipation (Note 6)	P _D	1.5	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State R _{θJA}	83	°C/W
		t < 10s 50	
Thermal Resistance, Junction to Case	R _{θJC}	14.5	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	I _D = 250μA, V _{GS} = 0V
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 60V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±16V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(th)}	1.0	—	3.0	V	I _D = 250μA, V _{DS} = V _{GS}
Static Drain-Source On-Resistance	R _{DS(ON)}	—	68	80	mΩ	V _{GS} = 10V, I _D = 4.5A
			70	100		V _{GS} = 4.5V, I _D = 3.5A
Diode Forward Voltage	V _{SD}	—	0.75	1.1	V	I _S = 12A, V _{GS} = 0V
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{ISS}	—	588	—	pF	V _{DS} = 30V, V _{GS} = 0V f = 1MHz
Output Capacitance	C _{OSS}	—	26.5	—		
Reverse Transfer Capacitance	C _{RSS}	—	20	—		
Gate Resistance	R _g	—	1.5	—	Ω	V _{GS} = 0V, V _{DS} = 0V, f = 1MHz,
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	5.6	—	nC	V _{DS} = 30V, I _D = 3A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	12.3	—		
Gate-Source Charge	Q _{GS}	—	1.7	—		
Gate-Drain Charge	Q _{GD}	—	1.9	—		
Turn-On Delay Time	t _{D(on)}	—	3.5	—	nS	V _{DD} = 30V, V _{GS} = 10V R _L ≅ 50Ω, R _G ≅ 20Ω
Turn-On Rise Time	t _r	—	4.1	—		
Turn-Off Delay Time	t _{D(off)}	—	35	—		
Turn-Off Fall Time	t _f	—	11	—		
Body Diode Reverse Recovery Time	t _{rr}	—	18	—	nS	I _S = 12A, di/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q _{rr}	—	12	—	nC	I _S = 12A, di/dt = 100A/μs

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

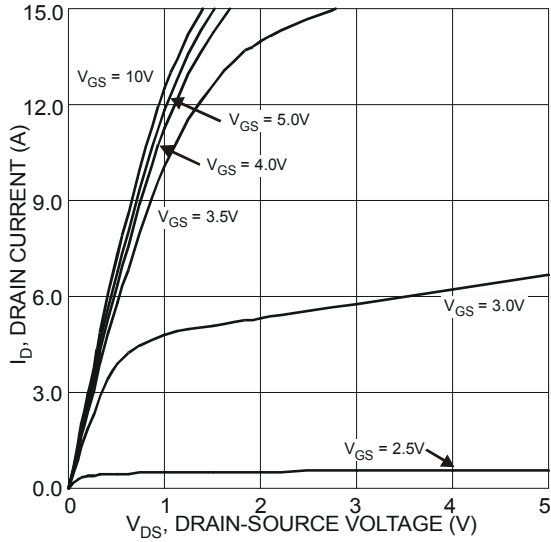


Figure 1 Typical Output Characteristic

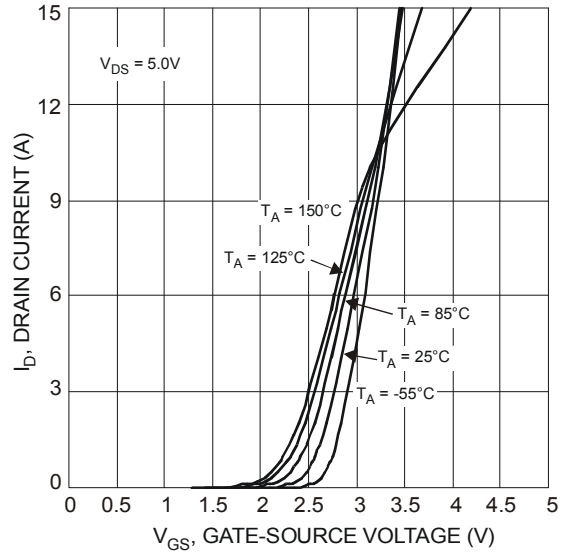


Figure 2 Typical Transfer Characteristics

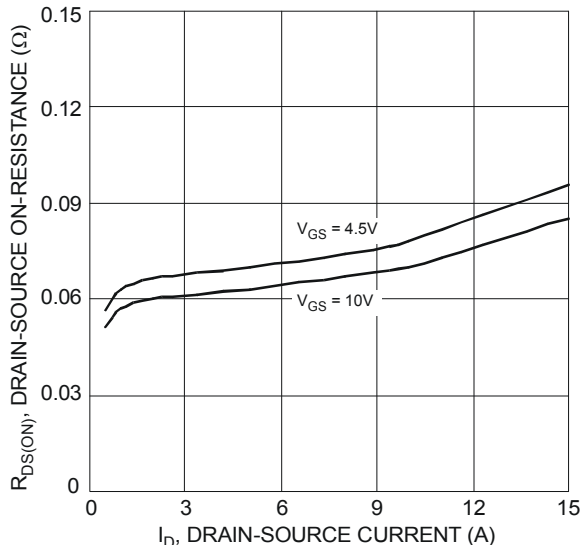


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

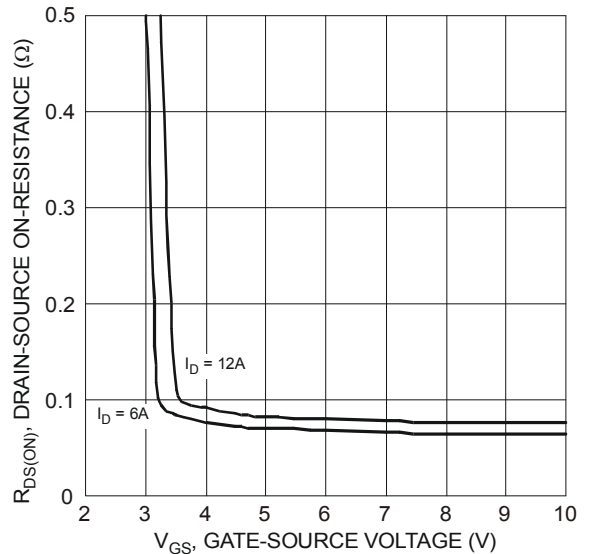


Figure 4 Typical Transfer Characteristics

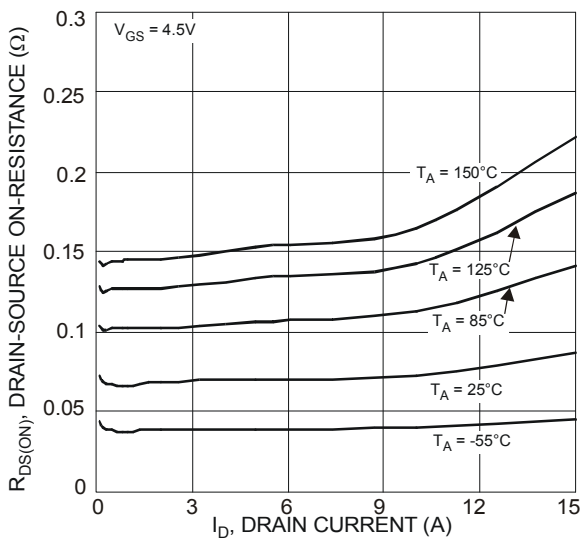


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

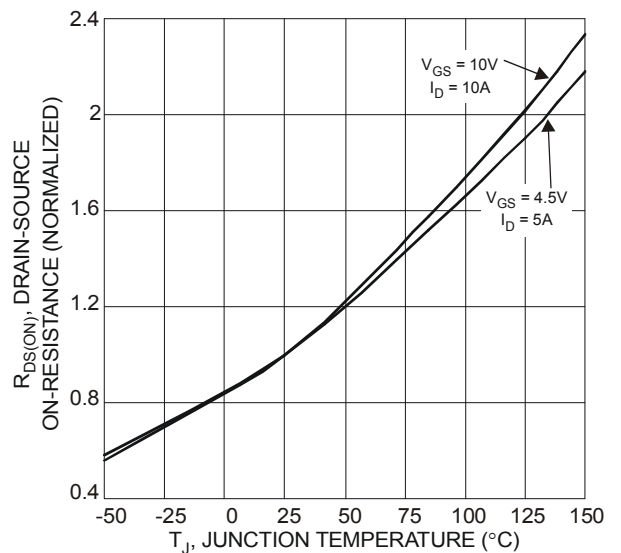


Figure 6 On-Resistance Variation with Temperature

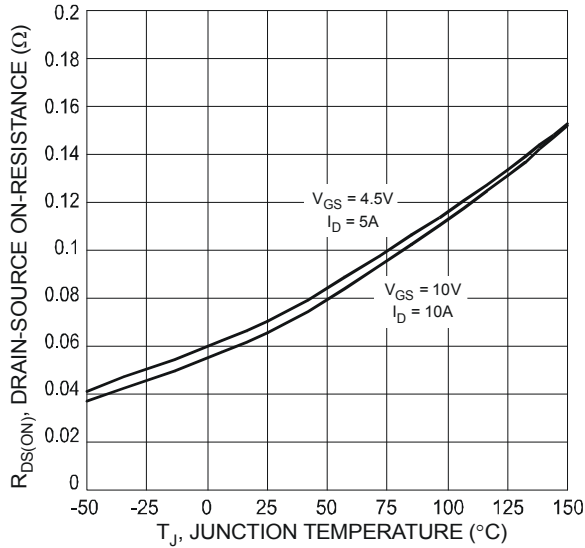


Figure 7 On-Resistance Variation with Temperature

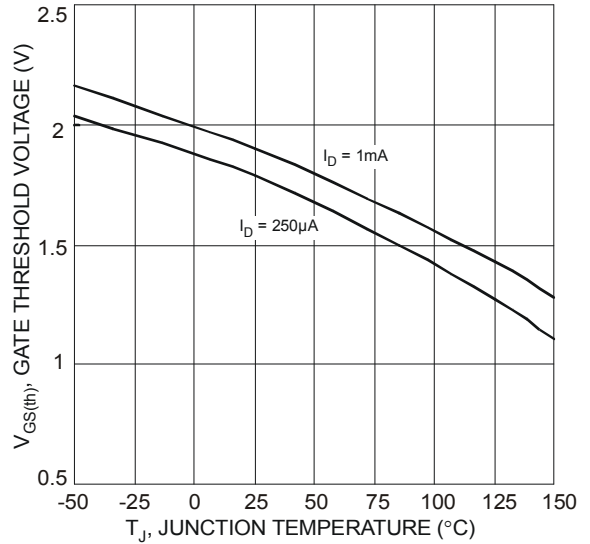


Figure 8 Gate Threshold Variation vs. Ambient Temperature

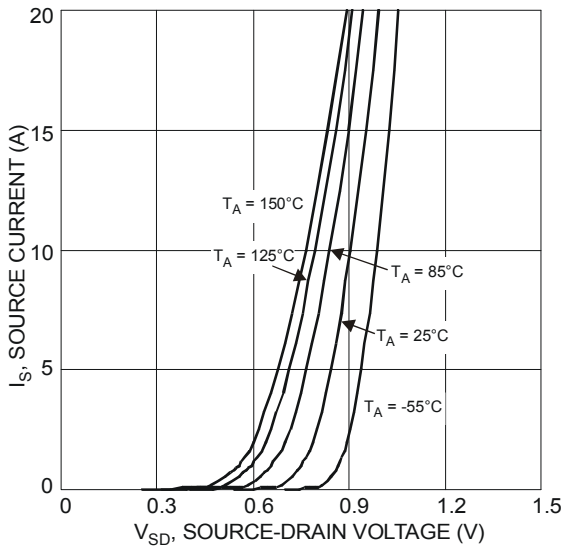


Figure 9 Diode Forward Voltage vs. Current

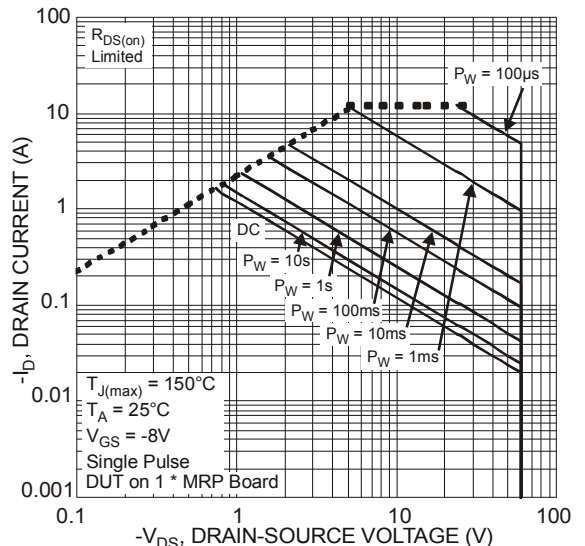


Figure 10 SOA, Safe Operation Area

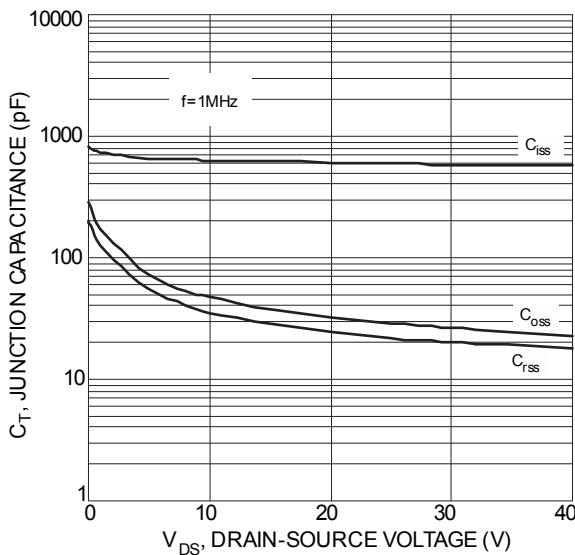


Figure 11 Typical Junction Capacitance

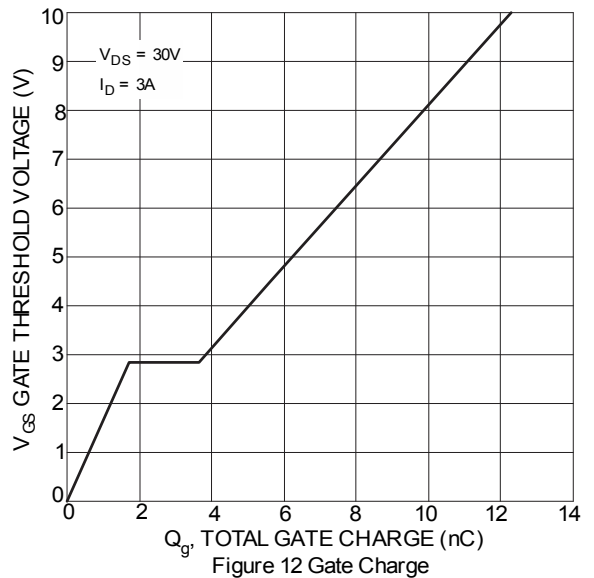
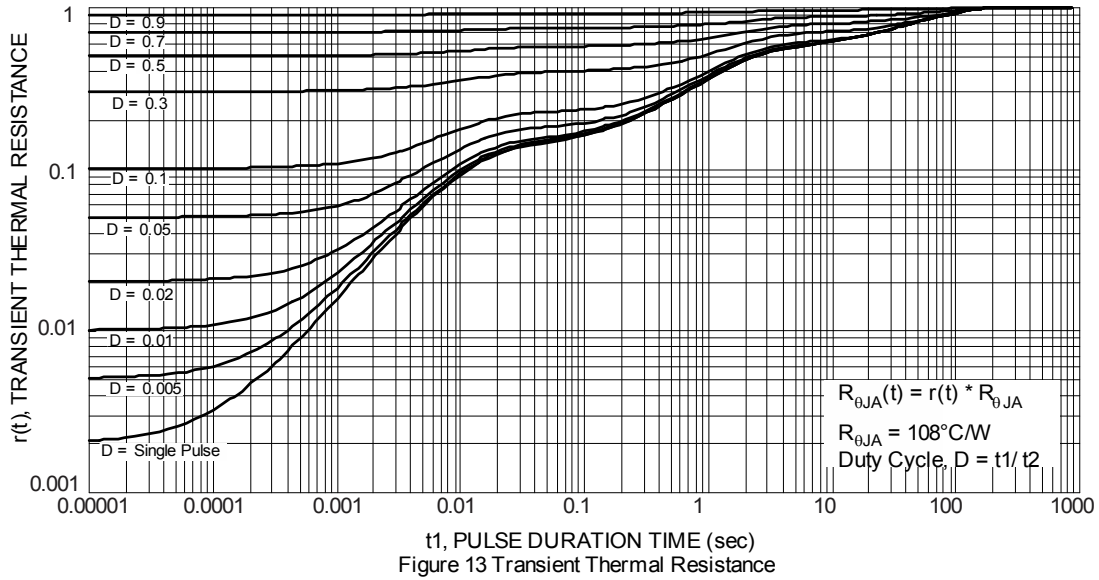
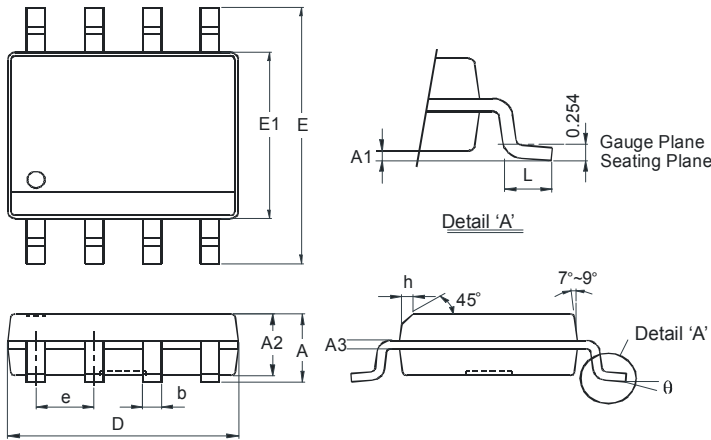


Figure 12 Gate Charge



Package Outline Dimensions

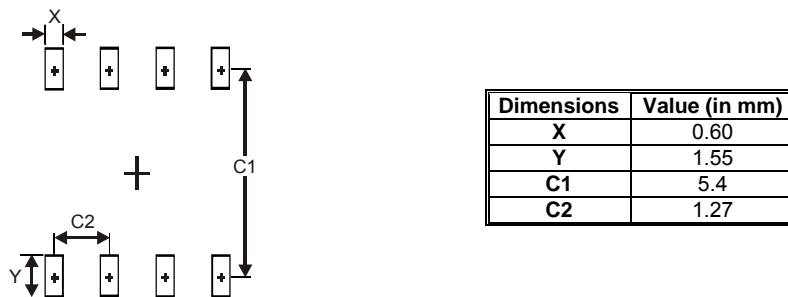
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SO-8		
Dim	Min	Max
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



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